IXYS

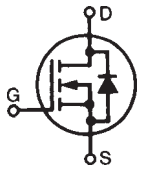
Advance Technical Information

Linear™ Power MOSFET w/Extended FBSOA

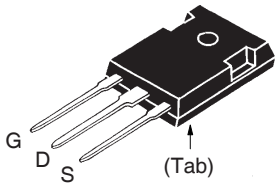
IXTH2N150L

V_{DSS} = 1500V
I_{D25} = 2A
$R_{DS(on)}$ ≤ 15Ω

N-Channel Enhancement Mode
Guaranteed FBSOA
Avalanche Rated



TO-247



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1500	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	2	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	6	A
P_D	T_C = 25°C	290	W
T_J		-55 to +150	°C
T_{JM}		+150	°C
T_{stg}		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in
Weight		6	g

Features

- Designed for Linear Operation
- International Standard Package
- Avalanche Rated
- Guaranteed FBSOA at 75°C

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

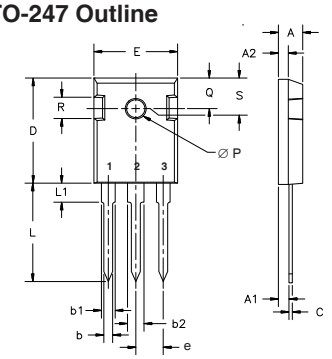
- DC Choppers
- DC-DC Converters
- Battery Chagers
- Programmable Loads
- Current Regulators
- Temperature and Lighting Controls

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	1500			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	6.0		8.5	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			15	μA
	T_J = 125°C			150	μA
$R_{DS(on)}$	V_{GS} = 20V, I_D = 0.5 • I_{D25}, Note 1			15	Ω

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 0.5 • I_{D25}, Note 1	0.4	0.7		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1470		pF
C_{oss}			92		pF
C_{rss}			30		pF
$t_{d(on)}$	**Resistive Switching Times**		33		ns
t_r	V_{GS} = 15V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		55		ns
$t_{d(off)}$	R_G = 10Ω (External)		85		ns
t_f			84		ns
$Q_{g(on)}$	V_{GS} = 20V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		72		nC
Q_{gs}			15		nC
Q_{gd}			30		nC
R_{thJC}				0.43	°C/W
R_{thCS}			0.21		°C/W

TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.	
SOA	V_{DS} = 1200V, I_D = 0.10A, T_C = 75°C, Tp = 5s	120			W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			2	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			8	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 2A, -di/dt = 100A/μs,		1.86		μs
I_{RM}	V_R = 100V, V_{GS} = 0V		24		A
Q_{RM}			22		μC

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

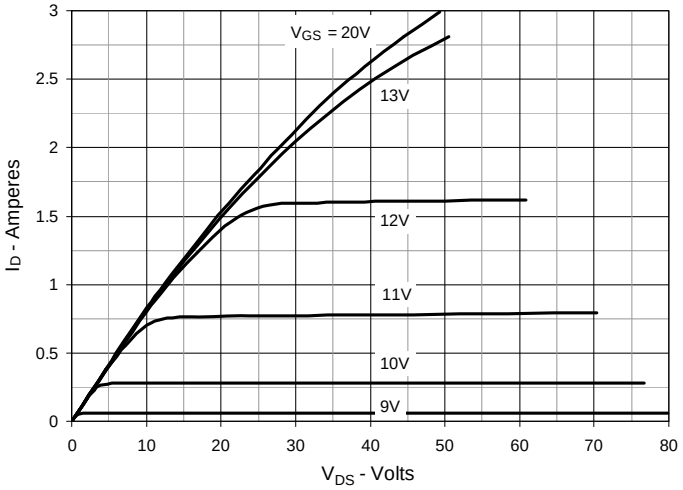


Fig. 2. Output Characteristics @ T_J = 125ºC

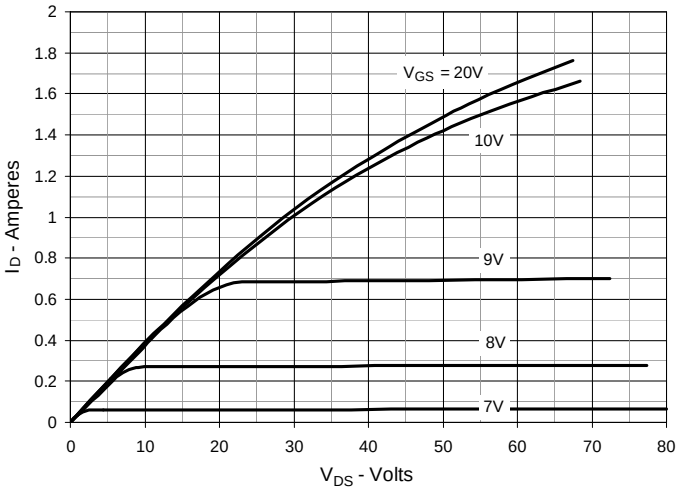


Fig. 3. $R_{DS(on)}$ Normalized to I_D = 1A Value vs. Junction Temperature

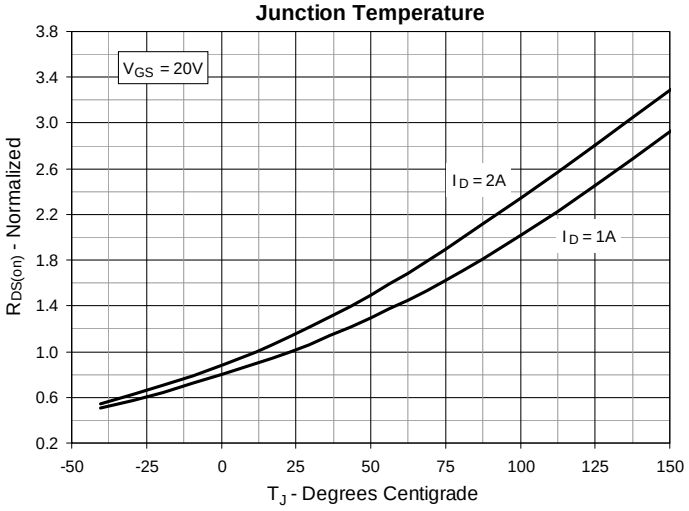


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 1A Value vs. Drain Current

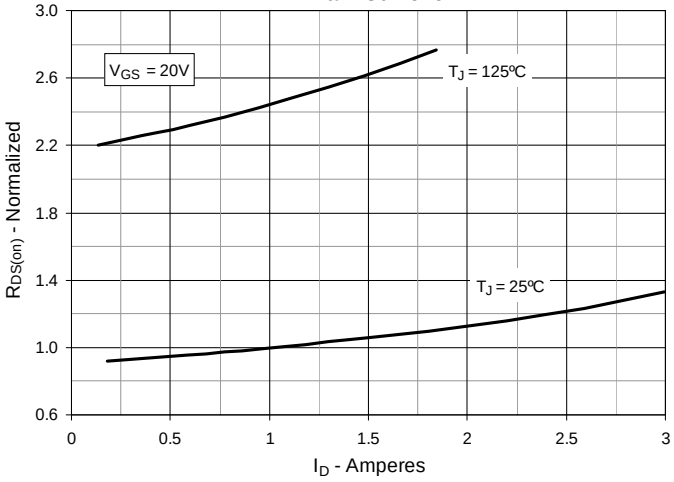


Fig. 5. Maximum Drain Current vs. Case Temperature

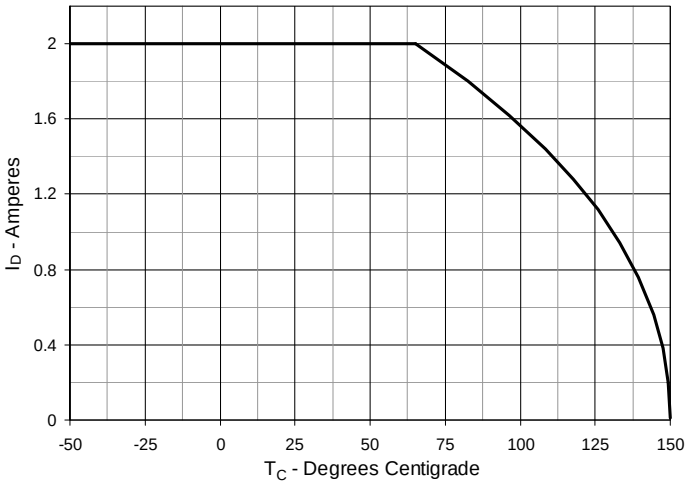
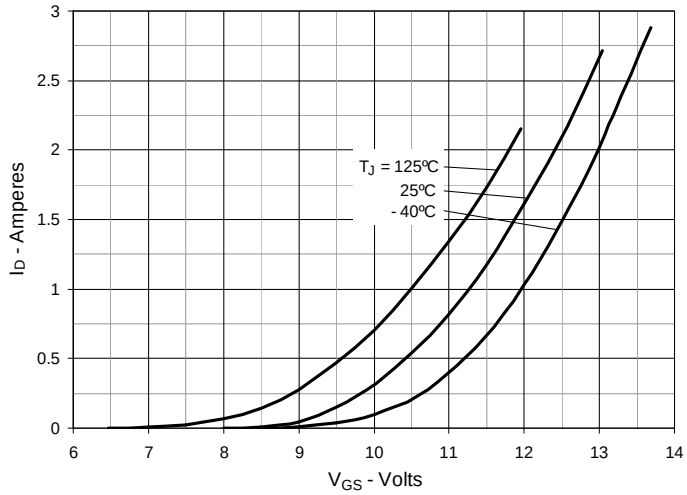


Fig. 6. Input Admittance



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Fig. 7. Transconductance

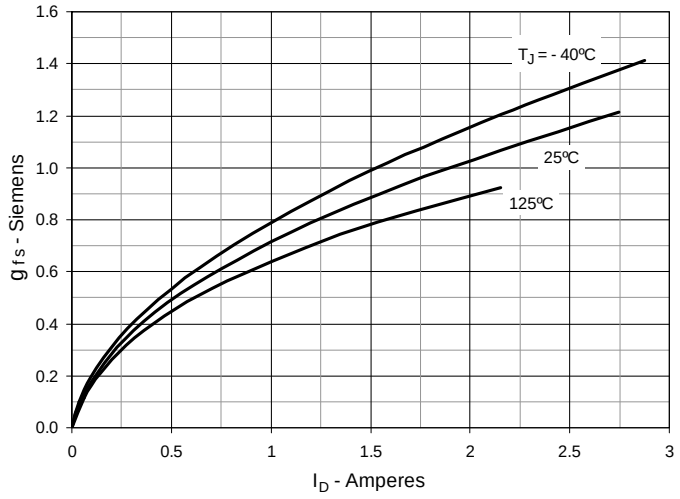


Fig. 8. Forward Voltage Drop of Intrinsic Diode

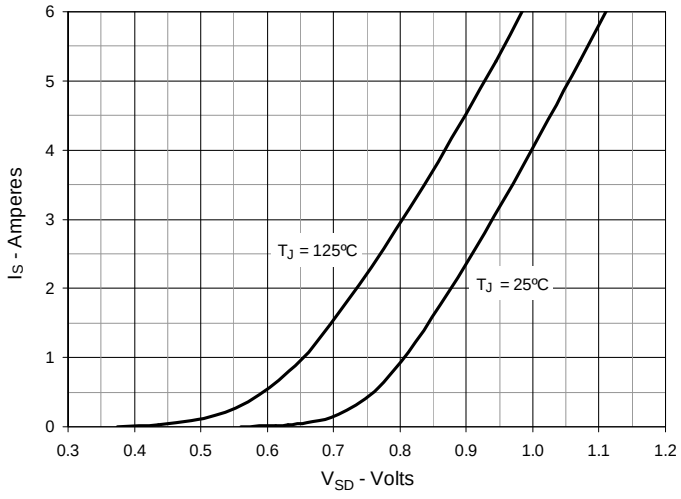


Fig. 9. Gate Charge

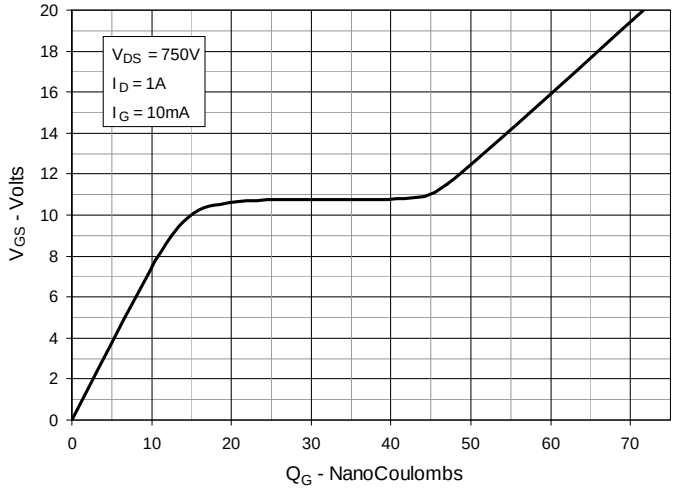


Fig. 10. Capacitance

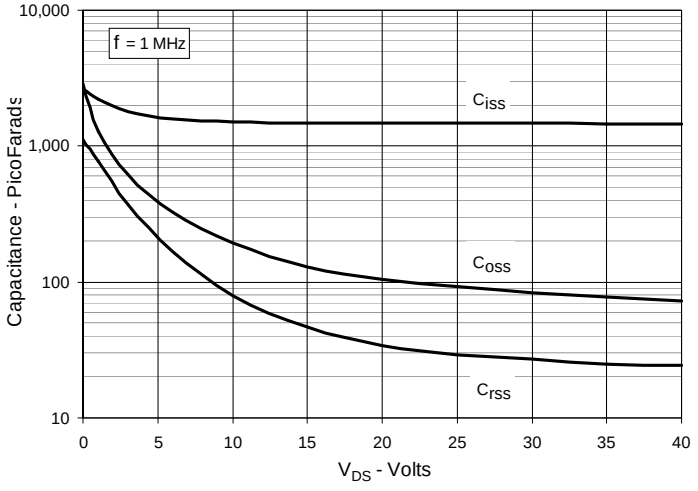
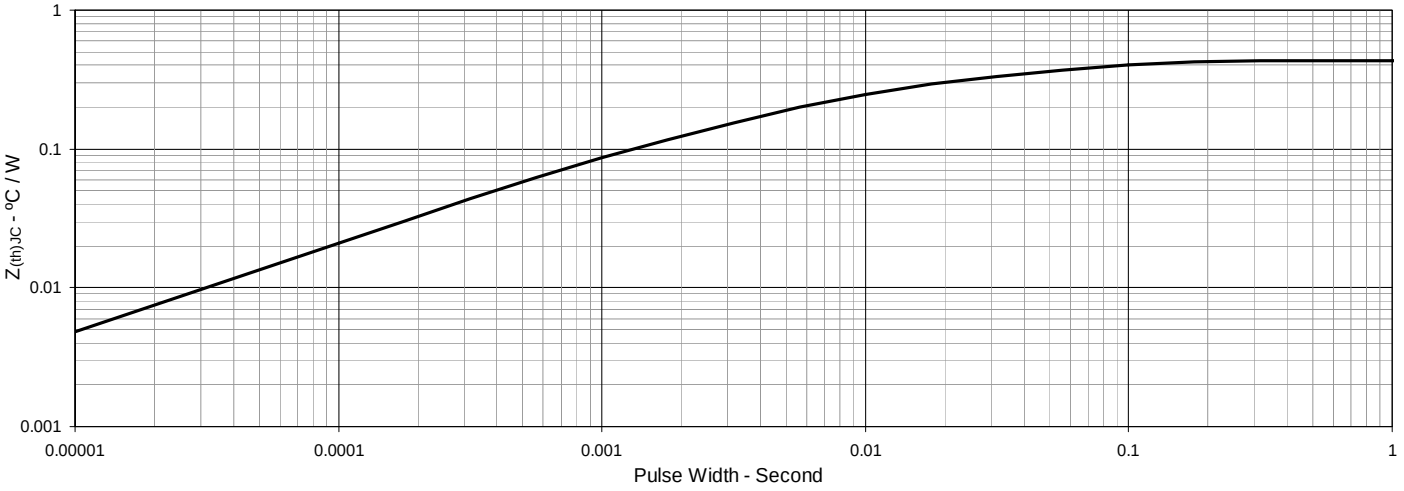


Fig. 11. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 12. Forward-Bias Safe Operating Area @ T_C = 25ºC

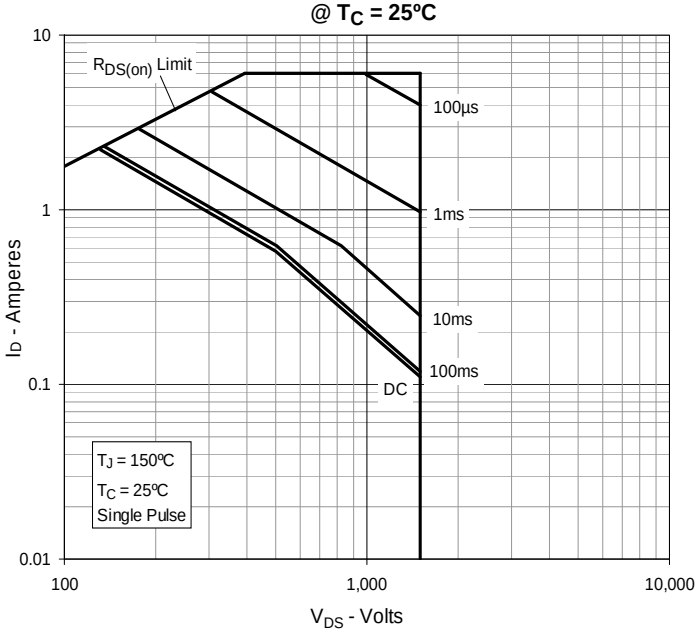
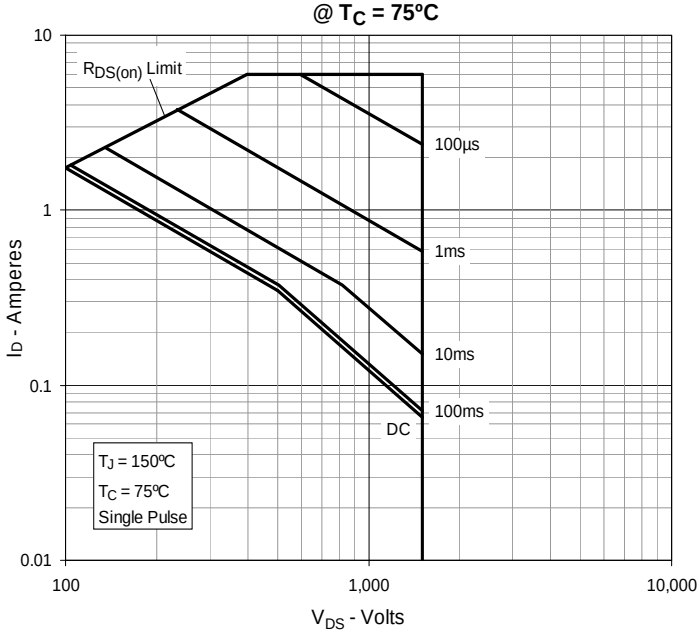


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 75ºC



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